



S.1. Raman graphene from polystyrene



S.2. High resolution transmission electron microscopy graphene from polystyrene



S.3. AFM image of graphene film from polystyrene where the thickness is measured doing a scratch in the film obtaining a value of 4-5 nm corresponding to a few layers graphene.



S.4. XRD graphene from polystyrene



S.5. TEM and SAED images of commercial G and BN sheets mixtures after pyrolysis.



S.6. EDS analysis of G-BN film on quartz substrate.



S7. Photographs of PS-BN (left) and G-BN superlattice (right) films.

Table S.1. Values of the impedance parameters determined for EIS spectra of G-BN superlattice and random G-BN assembly sheets in Figure 2, recorded in contact with air-saturated 0.10 M potassium phosphate aqueous buffer at pH 7.0; bias potential –0.60 V vs. Ag/AgCl using the equivalent circuits depicted in Figures 2a, 2b, respectively. Averaged values from three independent measurements.

| Element                      | G from PS                     | G-BN random                   | G-BN                       |
|------------------------------|-------------------------------|-------------------------------|----------------------------|
|                              |                               | assembly                      | superlattice               |
| <i>R</i> s (Ω)               | 200                           | 160                           | 250                        |
| <i>R</i> <sub>ct</sub> (Ω)   | 7900                          | 3800                          | 1450                       |
| $Q_{dl} (\Omega s^{-n}) (n)$ | 6.8 × 10 <sup>-5</sup> (0.92) | 8.6 × 10 <sup>-5</sup> (0.99) | $3.0 	imes 10^{-5}$ (0.81) |
| W (Ω s <sup>-1/2</sup> )     | $2.3 	imes 10^{-3}$           | $7.3 	imes 10^{-4}$           | $4.4 	imes 10^{-3}$        |